

SANYO

No.572D

2SA1016,1016K/2SC2362,2362K

PNP/NPN Epitaxial Planar Silicon Transistors

**High-Voltage Low-Noise Amp
Applications**

(): 2SA1016,1016K

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

		2SA1016, 2SC2362	2SA1016K, 2SC2362K	unit
Collector to Base Voltage	V_{CB0}	(-) 120	(-) 150	V
Collector to Emitter Voltage	V_{CE0}	(-) 100	(-) 120	V
Emitter to Base Voltage	V_{EB0}	(-) 5		V
Collector Current	I_C	(-) 50		mA
Collector Current(Pulse)	I_{CP}	(-) 100		mA
Collector Dissipation	P_C	400		mW
Junction Temperature	T_j	125		$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125		$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

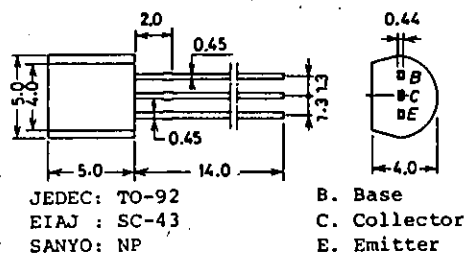
			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)80\text{V}, I_E=0$			(-) 1.0	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=(-)4\text{V}, I_C=0$			(-) 1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$	160*		960*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$		(110) 130		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(2.2) 1.8		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10\text{mA}, I_B=(-)1\text{mA}$			(-) 0.5	V
C-B Breakdown Voltage	$V_{(BR)CB0}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-) 120			V
		[A1016, C2362]				
		$I_C=(-)10\mu\text{A}, I_E=0$	(-) 150			V
		[A1016K, C2362K]				
C-E Breakdown Voltage	$V_{(BR)CE0}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-) 100			V
		[A1016, C2362]				
		$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-) 120			V
		[A1016K, C2362K]				
E-B Breakdown Voltage	$V_{(BR)EB0}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-) 5			V
Noise Level	$V_{NO(ave)}$	$V_{CC}=30\text{V}, I_C=1\text{mA}, R_g=56\text{k}\Omega$ $V_G=77\text{dB/1kHz}$			35	mV
Noise Peak Level	$V_{NO(peak)}$	" " "			200	mV

* The 2SA1016,K / 2SC2362,K are classified by 1mA h_{FE} as follows :

160	F	320	280	G	560	480	H	960
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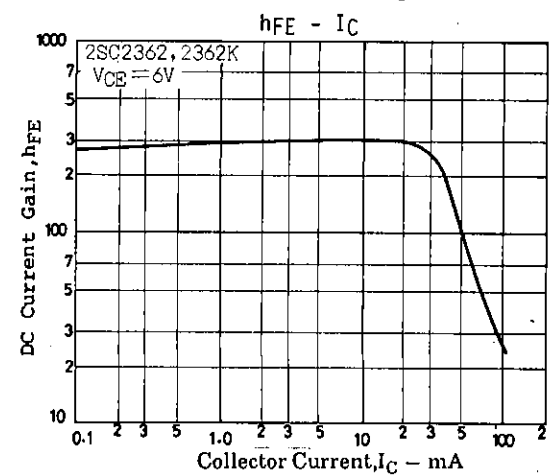
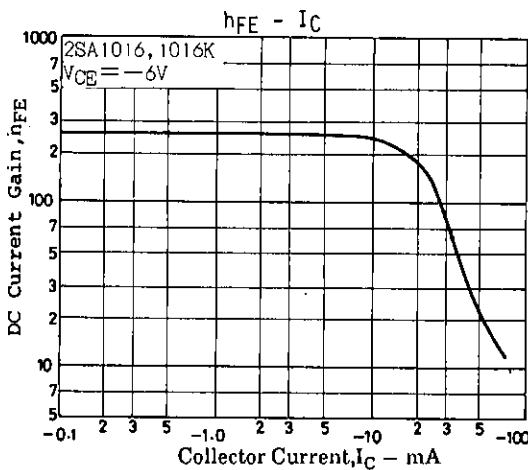
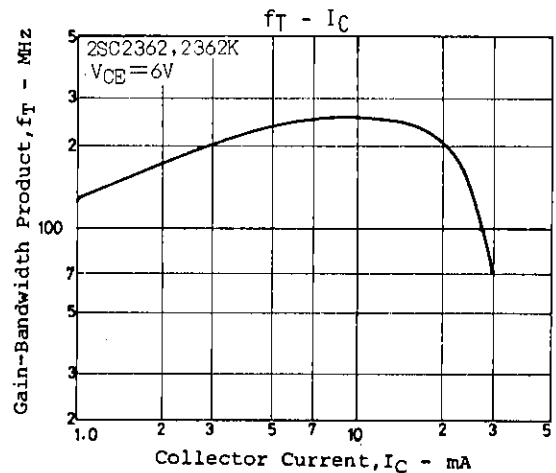
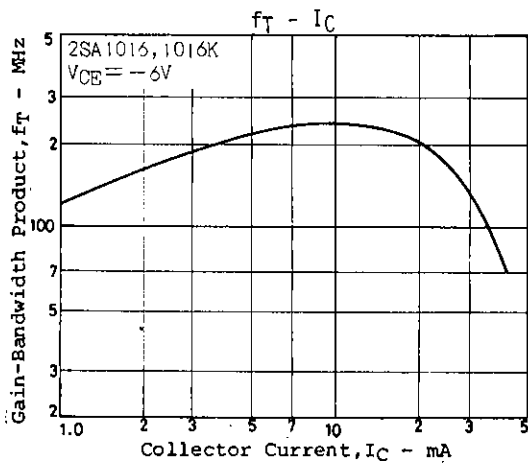
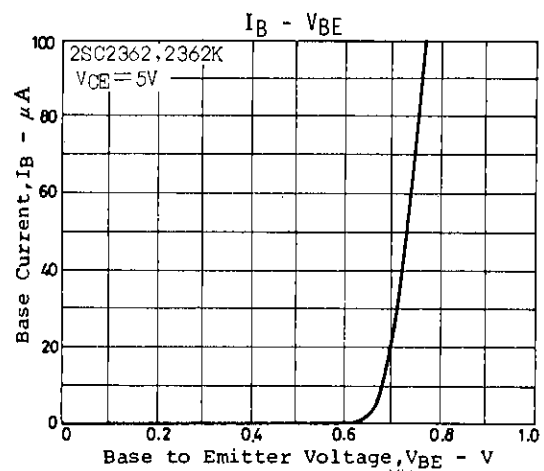
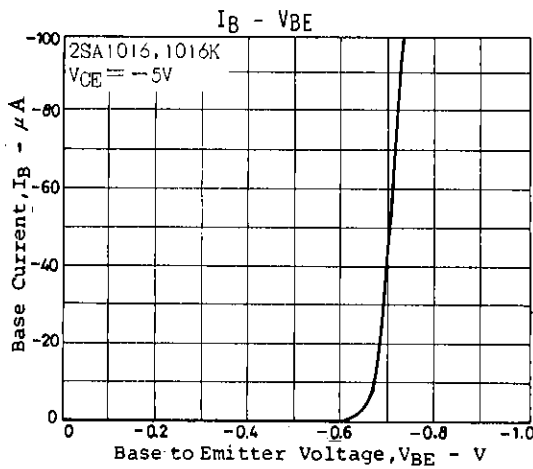
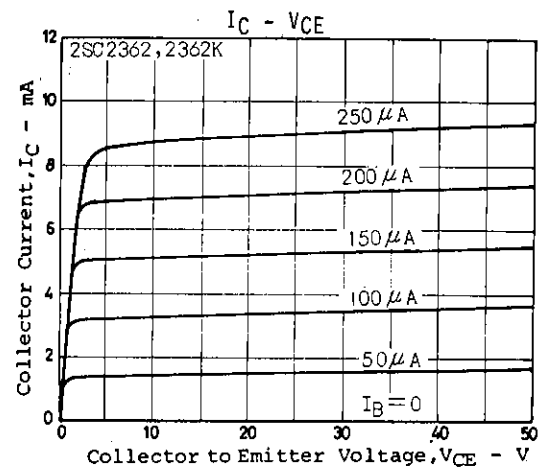
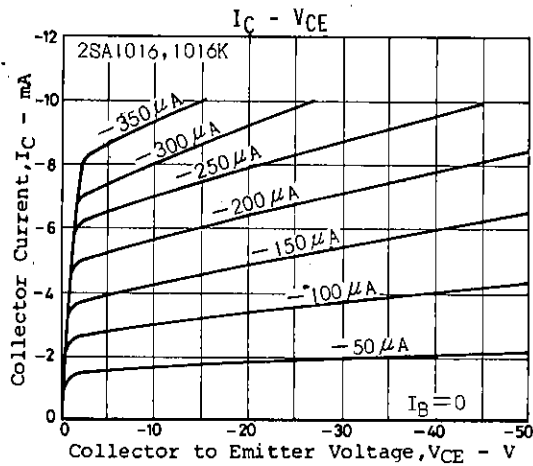
Package Dimensions
(unit: mm)

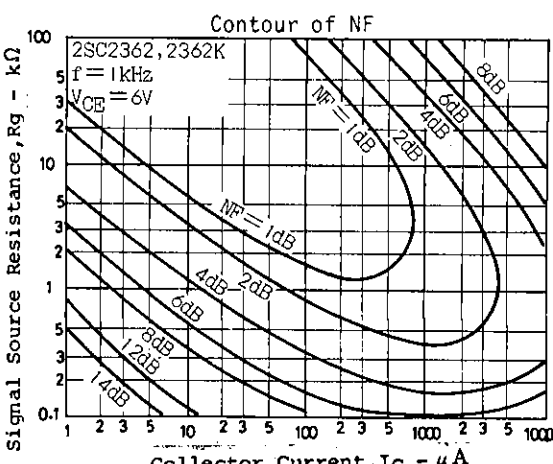
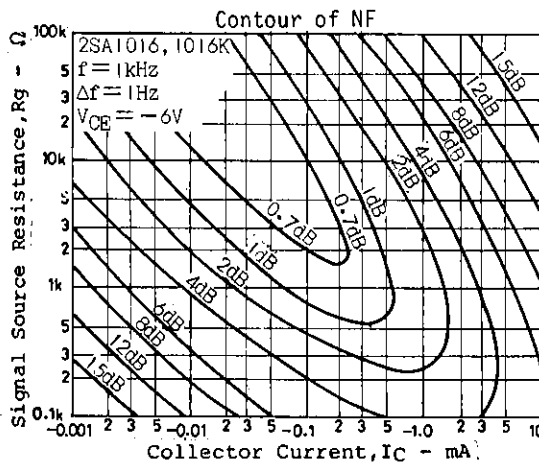
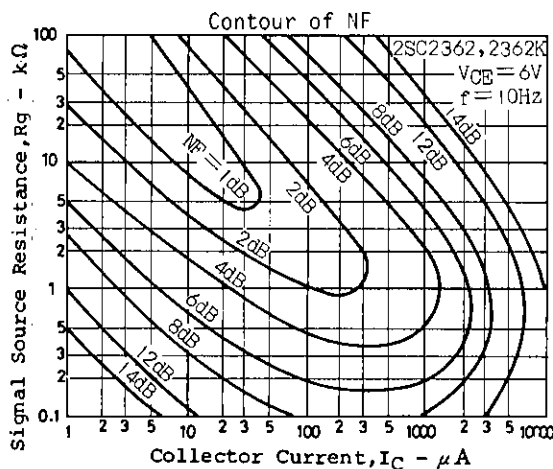
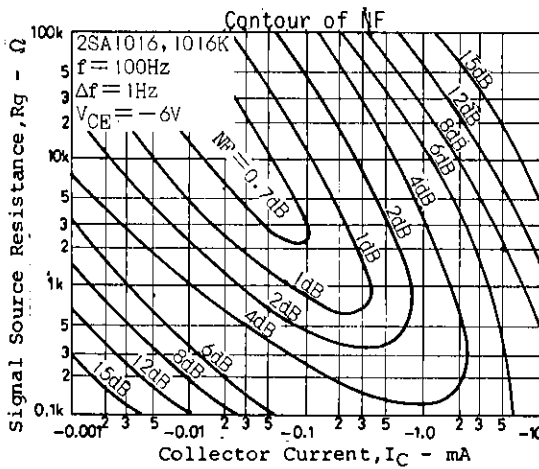
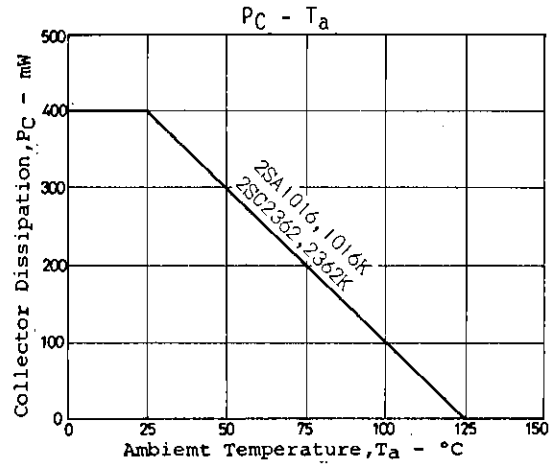
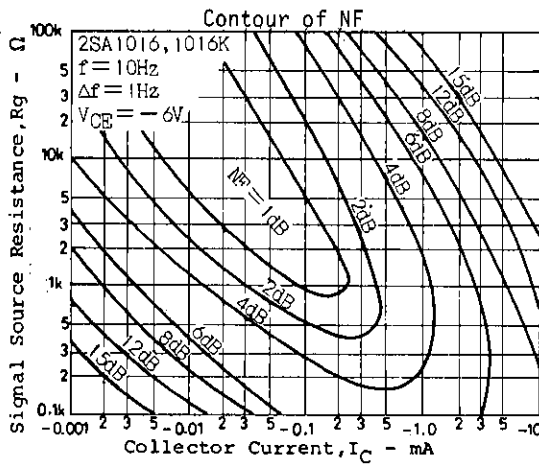
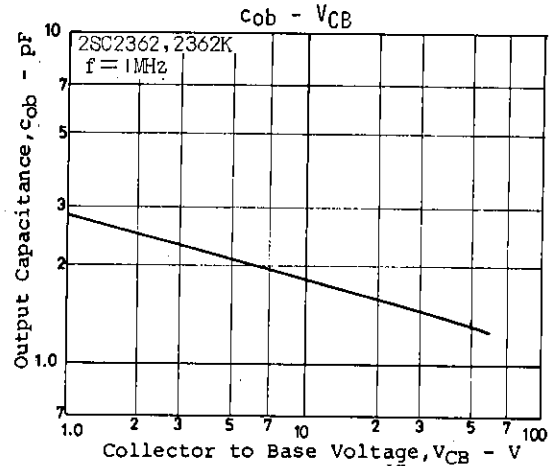
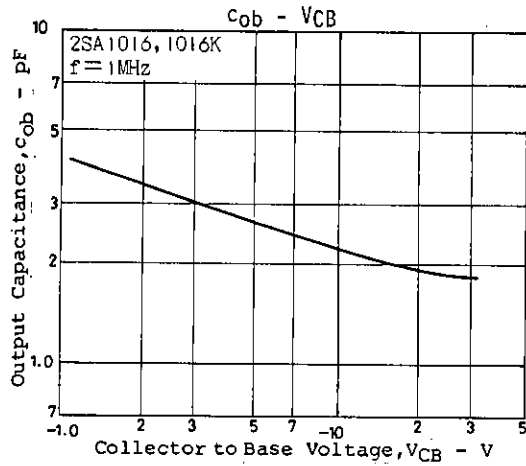
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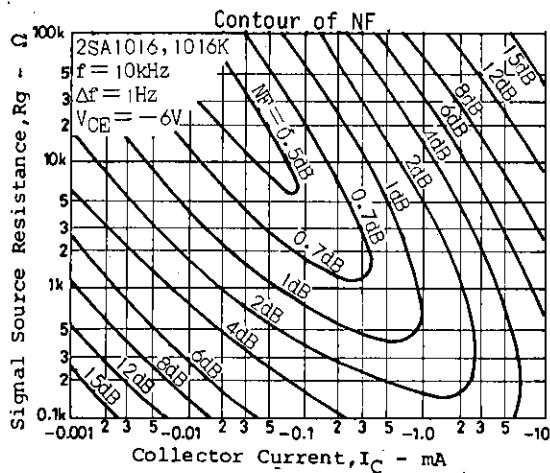
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3187AT/3075KI/1313KI No.572-1/4







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